



Development of MIP Timing Detector for the CMS Phase-2 Upgrade

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MIP Timing Detector for CMS Phase-2 Upgrade



- Important to maintain detector performance during HL-LHC running
 - Time information will help to reduce pileup effects from approximately 200 simultaneous interactions
- MIP timing detector (MTD) consists of barrel timing layer (BTL) and endcap timing layer (ETL), providing 30-50 ps time resolution per track
 - BTL: LYSO crystal scintillator + SiPM readout
 - ETL: Silicon based sensor (LGAD) + ASIC readout

MTD Physics motivation: pile-up mitigation





- Important to maintain detector performance during HL-LHC running
 - Time information will help to reduce pileup effects from approximately 200 simultaneous interactions



The display of an event with a Higgs boson produced in the VBF process on top of 200 pile-up collisions.

MTD Physics motivation: pile-up mitigation



- □ The mitigation of pile up effect improves all physics objects
- 4D vertexing (position+time) can remove
 - Spurious pileup tracks from "isolation cone" around leptons
 - Rejects spurious jets formed from pileup particles.

MTD Physics motivation: particle ID



MTD can provide significant improvement for particle ID

• heavy ion charm tag.

□ Significant gains for searches for long-lived new particles.

Mip Timing Detector (MTD) Project



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Overview of endcap timing layer (ETL)

- Two layers of silicon sensors covering 1.6 < |η| < 3.0
- Sensors mounted in rows on each face of Al cooling disks
- Readout boards placed between sensor rows, staggered wrt opposite face for full sensor coverage.
- Two such disks to provide average of 1.8 hits per track.
- Mounted on neutron moderator upstream of the CE, in an independently cooled and accessible volume.



ETL structure



ETL z-profile

Element	Elements in Z	Thickness [mm]
1	Thermal screen	20
y	Gap between thermal screen and front disc	1
2	Front face of electronics of the front DEE	8**
3	Front disc	7.5
4	Rear face of electronics of the front DEE	8
	Gap between front and back discs	1
5	Front face of electronics of the back DEE	8
6	Back disc	7.5
7	Rear face of electronics of the back DEE	8
	Gap between cables and back disc	1
8 + 9	Patch panels 0 + cables [9] + moderator [8] at the innermost section	21
10	Back support plate	5
	Gap between ETL back support plate and HgCal thermal screen	3***
	Total	99

* All gaps (1mm) are an additional clearance for disc deformation while transporting and rotating. More detailed study whether 1mm is sufficient are needed.

** Maximum thickness of the on-detector electronics should not exceed 8mm, services included.

*** It was simulated that a support structure of HgCal at cold operations shrinks by 2-3mm in Z while its thermal screen stays in the same position.

Components that still need prototyping to finalize the z-profile.

Detector layout Front layer

•	Short (3 modules) SHs	15
•	Standard (6 modules) SHs	35
•	Large (7 modules) SHs	28

- * Small SHs possibly to be placed as well at the inner radius in order to maximize the coverage
- · More detailed model of the power board is required in order to verify possible clashes with the detector mechanics



Detector layout Rear layer

- Short (3 modules) SHs
- Standard (6 modules) SHs 35
- Large (7 modules) SHs 27

16

 More detailed design of the service hybrid attachment to the discs shall be developed (amount and location of bolts/pins) to verify whether rows can be shifted up or down in order to maximize the coverage at the inner radius



ETL Module assembly

Fermilab, SiDet, Detector test Area



- □ LGAD+ASIC assemblies mounted on AIN (Aluminum Nitride) carrier plates
- □ Aerotech 3+1 axis gantries were used for ETL module assembly
- Labview program for the set-up and motion of gantry required for module assembly

Module design

LGADs bump bonded to 2 ETROCs then assembled into modules.



- Wire bonds encapsulated and sensors protected with AlN cover
 - Ruggedized AlN sandwich.
 - Active components off the module.
- Designed to be easily buildable.

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Service hybrids

 Service hybrids providing control, readout, and power, are mounted between rows of modules.



Parameters for time resolution determination



Jitter in ASIC is measured from preamplifier and discriminator

Noise source

Time walk: the voltage value V_{th} is reached at different times by signals of different amplitude

Jitter: the noise is summed to the signal, causing amplitude variations



Mostly due to electronic noise



Due to the physics of signal formation

Endcap Timing Layer ReadOut Chip (ETROC)



ETROC Block Diagram

- □ Total ETROC size: 16 X 16 pixel cell
 - One pixel cell size: 1.3mm X 1.3mm to match the LGAD sensor pixel size
- □ Targeting signal charge (1MIP): ~6 fC
- TDC (time-to-digital converter) range
 - ~5 ns TOA (time of arrival)
 - ~10 ns TOT (time over threshold)

ETROC Development Plan





ETROCO

- Submitted in Dec. 2018
- Analog Front-end
- Tests by far confirmed functionality
- First round beam test early 2020



ETROC1

- Submitted in Aug. 2019
- 4 X 4 pixel array with full front-end including TDC
- Chips received middle Dec 2019
- TDC block works well
- Single pixel full chain testing on going, and followed by 4x4 array testing



- ETROC2
 - Aim to submit in Q1 2021
 - Designed to be compatible with 16 X 16 pixel array with
 - full functionalities
- ETROC3
 - Aim to submit in Q1 2022
 - Pre-production version

KNU group contributes on studies of the ETROCO/1 since June, 2019

Low Gain Avalanche Diode (LGAD) Sensors

Sensor producer

HPK (Hamamatsu, Japan), FBK (Italy), CNM (Spain), NDL (China) 0

LGAD characteristics

- Precision position reconstruction and timing resolution
- Highly improved radiation tolerance
- Large signals with low noise
- Thin implanted gain layer of overall thickness of 35–50 μm
- The additional doping layer present at the n-p junction
 - Generates the high field necessary to achieve charge multiplication.



HPK 4x4 sensor array($1 \times 3 mm^2$ pads)



FBK 2x8 sensor array($2 \times 2 mm^2$ pads)



Charge Multiplication

- But devices with charge multiplication were already there:
 - Avalanche Photodiodes (APDs)
 - Photodiodes Gain=1
 - APD Gain=100-1000
 - Geiger mode (SPAD/SiPM) Gain~1E7



High field obtained by adding an extra doping layer

- E ~ 300 kV/cm, closed to breakdown voltage
- For HEP (particle detection, not photons)
- Keep charge information (linearity, not Geiger mode)
- · But APDs are too noisy due to gain

Initial idea was APD with "low Gain" (~10-20) to compensate charge loss after irradiation



Low Gain Avalanche Detectors (LGAD)

- However, colleagues at UCSC [1] proposed the technology for timing
 - Very fine segmentation not needed...

Time resolution:

$$\sigma_{\rm det}^2 = \sigma_{\rm Landau}^2 + \sigma_{\rm elec}^2$$

$$\sigma_{elec}^2 = \left(\frac{t_{rise}}{S/N}\right)^2 + \left(\left[\frac{V_{thr}}{S/t_{rise}}\right]_{RMS}\right)^2 + \left(\frac{TDC_{bin}}{\sqrt{12}}\right)^2$$

Timewalk Jitter

- Need fast signal and excellent S/N
 - A multiplication layer increases signal slope
 - But low gain to reduce noise
 - Time-walk contribution can be corrected
- Thin sensors (50 µm) further reduce intrinsic Landau contribution to resolution

[1] Hartmut F-W Sadrozinski et al, 2018 Rep. Prog. Phys. 81 026101 [2] F. Cenna et al, NIM A796 (2015) 149-153



Silicon Detectors after Irradiation

- Irradiation degrades the signal of silicon detectors
- Recover it by increasing bias voltage
 - · Hit limit of PS or device breaks
- But while investigating thin devices (epitaxial) for the HL-LHC, *Lange et al.*, found that highly irradiated samples, could achieve CCE>1 at high bias voltages (>1E5 V/cm)
 - Charge multiplication by impact ionization



People quickly started thinking if the "charge multiplication" effect could be exploited to create more radiation hard silicon detectors....

Test beam with 120 GeV proton at Fermilab



LGAD sensor test with 120 GeV proton beam

FNAL test beam facility (FTBT)



Beam properties at FTBT

- 120 GeV proton beam
- Beam width : few mm to few cm
- 100k protons per 4 second spill per minute

Strip and Pixel telescope

• Provides proton track position

Extra strip layer after cold box

- Prevent scattered proton
- Measure efficiency ~99%

Photek Micro-Channel Plate (MCP)

 Provided a very precise reference timestamp (~10 ps)

Cold box (Environmental Chamber)

• LGAD sensor and MCP are mounted

LGAD prototyping campaigns



- Optimization of gain layer & thickness for best time resolution
- Improving radiation hardness, Developing large arrays of sensors

Prototypes satisfy

- Time performance < 40 ps
- Uniform performance of all sensor surface

Irradiated FBK 2x8 arrays sensor test

Silicon Detector Facility (SiDet)

- Validation of beta source measurement
 Irradiated FBK 2x8 arrays sensor test
 - Signal amplitude
 - Hit efficiency
 - Timing performance
 - Radiation damage

Prototype LGAD Sensor testing







Validation of beta source measurement



- Compared same sensor with same condition
 - HPK 3.1 sensor on UCSC board (-20 degree condition)
- Signal properties of beta source and protons are almost consistent
 - Small difference in resolution

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Time Resolution of LGAD Sensor

□ Time resolution is obtained between timestamp of LGAD and MCP □ Δt distribution fit with Gaussian to obtain width σ_t □ Uniform at ~40 ps on 16-channel board



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Irradiated FBK 2x8 arrays sensor test – signal amplitude

30

22

x [mm]





2D mpv map of average amplitude



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Irradiated FBK 2x8 arrays sensor test - Hit efficiency



x [mm]

13.5

15.5

x [mm]

Irradiated FBK 2x8 arrays sensor test – Timing performance

- Timing uniformity with respect to MCP reference
 - Time difference between time stamp of LGAD and MCP
 - $\circ \ \Delta t = |t_1(LGAD) t_0(MCP)|$
 - $\circ\,$ Time resolution : Δt distribution fit with Gaussian to obtain width σ_t
 - LGAD, MCP time stamp
 - Larger signals (LGAD) reach threshold earlier
 - Constant Fraction Discriminator (CFD)
 Threshold as fraction of peak amplitude





Irradiated FBK 2x8 arrays sensor test – Timing performance



Latest FBK production maintains less than 40 ps resolution for the entire lifetime

Irradiated FBK 2x8 arrays sensor test – Collected charge



AC-LGAD strip sensor



Photograph of the AC-LGAD sensor. The seventeen individual strips are referenced according to labels 0 to 16, from left to right.

2 100 mV 22.9 < y < 24.1 mm - Any Strip 20.48 < x < 20.62 mm Anv Strip Center Strip 100 Left Strip Right Strip Efficiency, Efficiency, 0.5 0.5 22 20.2 20.4 20.6 20.8 23 24 25 21 x [mm] y [mm]

Cross section of a segmented AC-LGAD. For simplicity, only three AC electrodes are shown, and the figure is not to scale.



Combined signal effciency of adjacent strips as a function of the proton track x and y position, for signals with amplitudes above a 100 mV threshold. In (a) individual strip effciencies are also shown, and vertical grey bands indicate the strip positions in the x-direction.

(b) Combined efficiency in y direction.

⁽a) Combined efficiency in x direction.

AC-LGADs for Electron Ion Collider

□ AC-LGAD based Time of Flight (TOF) can provide the Particle ID for every particle in EIC.

- based on 30 ps timing resolution
- $^\circ\,$ Ideally coarse pitch (500 μm , 1-2 cm strips) for sparse readout
- $\circ\,$ TOF can be used tracking layer (~20 μm resolution)
- TOF ID complements Cherenkov-based ID for soft particles.



AC-LGADs for Electron Ion Collider

AC-LGAD TOF Detectors for EIC – eRD112



Barrel TOF Single layer with 30 ps resolution and $2\%X_0$ material budget per layer

Forward TOF Double layer with 25 ps resolution and $5\%X_0$ material budget per layer

Backward TOF

Double layer with 25 ps resolution and $5\%X_0$ material budget per layer

START Time 20 ps resolution Barrel TOF simulation (eta=0)



Thank you

back up

Silicon detectors in High Energy Physics (HEP)

- Innermost layers of HEP accelerator-based experiments require:
 - Position resolution, rate capability, compactness, low material budget, radiation hardness, etc
- Technology of choice: silicon pixel sensors



PN Junction Diode





ETL Sensor Test at FNAL

Silicon Detector Facility (SiDet)

- □ LGAD Sensor characterization with beta source measurement
 - Ensure a guaranteed level of readout accuracy over various operating condition
- Measure signal amplitude, risetime, resolution, signal-nose ratio, etc

Fermilab Test Beam Facility (FTBF)

Designated beamtime Feb 19-25 (primary user) 2020

- Extensive characterization of ETROC0 with LGADs
- Characterization of irradiated non-uniform FBK 2x8 arrays
- Validation of beta source measurement with HPK 3.1 sensor.

Parasitic running Feb 26 – March 6 2020

• Sensor test for next generation LGAD





LGAD Testing & Module assembly at Fermilab

Photodetector timing lab

<image>

Testing board assembly LGAD sensor testing ETL module assembly

Detector test Area

Assembly - Gantry based

• Gantry Systems at UNL & FNAL being developed for module assembly



Assembly - Gantry based

• Gantry Systems at UNL & FNAL being developed for module assembly



Assembly - Gantry based

- Gantry Systems at UNL & FNAL being developed for module assembly
- Tooling currently being fabricated for glue-based assembly of TDR modules
 - Tooling for Tamale design would only require minor modifications



ETL Bump-Bonding Studies

- Goal: Determine bump-bonding scheme for LGAD/ETROC interface
 - Choices: # bumps / pixel? Bump arrangement?
 - Tests: electrical connectivity/yield, thermal, and mechanical properties
- Bump-bonding "dummies" production:
 - "Dummy" Si "sensors" and "chips" with real dimensions and pixel pitch for electrical/thermal/mechanical testing
 - Multiple vendors: CNM and BNL for wafer fabrication, Micross and ICAE Barcelona for bump-bonding/assembly
 - Variations in bump # and layout, vendors
 - ~120 module-sized test structures in total
- Bump-bonding "dummies" testing:
 - Automated tests of bump electrical conductivity using resistor columns (to be repeated after thermal and

mechanical tests)

If one bump is missing, the current is "forced" in the high resistance path Every other pad there is a "short": Measuring the resistance between the first and the last pad will give an indication of all the missing bump

Part of the assemblies are "SINGLE BUMP": the bumps are placed to simulate 1 bump pe 1.3x1.3 mm2 pixel

Other assemblies are "DOUBLE BUMPS I bumps per pixel



wafer

ssembly







Mechanical Shear Stress Measurements

https://indico.cern.ch/event/1020750 https://indico.cern.ch/event/1007814





Component Cataloging

All samples (sensors, chips, assemblies) were tagged and registered in a db where we can store info, notes, pictures, test results, etc.,



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Linear regime



performed on one sample: no appreciable change in mechanical performance 11